Guan-Bo Lin

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/11600900/publications.pdf

Version: 2024-02-01

18	537	933447	996975
papers	citations	10 h-index	15 g-index

18	18	18	510
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Analytic model for the efficiency droop in semiconductors with asymmetric carrier-transport properties based on drift-induced reduction of injection efficiency. Applied Physics Letters, 2012, 100, .	3.3	139
2	Asymmetry of carrier transport leading to efficiency droop in GaInN based light-emitting diodes. Applied Physics Letters, 2011, 99, .	3.3	129
3	Identifying the cause of the efficiency droop in GaInN light-emitting diodes by correlating the onset of high injection with the onset of the efficiency droop. Applied Physics Letters, 2013, 102, .	3.3	75
4	Efficiency droop in AlGaInP and GaInN light-emitting diodes. Applied Physics Letters, 2012, 100, .	3.3	63
5	Effect of Quantum Barrier Thickness in the Multiple-Quantum-Well Active Region of GaInN/GaN Light-Emitting Diodes. IEEE Photonics Journal, 2013, 5, 1600207-1600207.	2.0	30
6	Optically functional surface composed of patterned graded-refractive-index coatings to enhance light-extraction of GaInN light-emitting diodes. Journal of Applied Physics, 2011, 110, .	2.5	20
7	Onset of the Efficiency Droop in GaInN Quantum Well Light-Emitting Diodes under Photoluminescence and Electroluminescence Excitation. ACS Photonics, 2015, 2, 1013-1018.	6.6	20
8	GaInN light-emitting diodes using separate epitaxial growth for the p-type region to attain polarization-inverted electron-blocking layer, reduced electron leakage, and improved hole injection. Applied Physics Letters, 2013, 103, .	3.3	18
9	Method for determining the radiative efficiency of GaInN quantum wells based on the width of efficiency-versus-carrier-concentration curve. Applied Physics Letters, 2012, 101, .	3.3	15
10	â€œU-turnâ€•feature in the efficiency-versus-current curve of GaInN/GaN light-emitting diodes. Applied Physics Letters, 2014, 105, .	3.3	13
11	Polarization-Engineered High-Efficiency GaInN Light-Emitting Diodes Optimized by Genetic Algorithm. IEEE Photonics Journal, 2015, 7, 1-9.	2.0	6
12	Analysis of parasitic cyan luminescence occurring in GaInN blue light-emitting diodes. Journal of Applied Physics, 2012, 112, 074512.	2.5	4
13	Distinct U-shape efficiency-versus-current curves in AlGaN-based deep-ultraviolet light-emitting diodes. Optics Express, 2015, 23, 15398.	3.4	3
14	Effect of a p-type ZnO insertion layer on the external quantum efficiency of GaInN light-emitting diodes. Applied Physics Express, 2015, 8, 092102.	2.4	1
15	Temperature Dependence of Efficiency in GaInN/GaN Lightâ€Emitting Diodes with a GaInN Underlayer. International Journal of Applied Ceramic Technology, 2016, 13, 234-238.	2.1	1
16	S6-G4: High injection and efficiency droop in GaInN light-emitting diodes. , 2014, , .		0
17	The beneficial effects of a p-type GaInN spacer layer on the efficiency of GaInN/GaN light-emitting diodes. Current Applied Physics, 2015, 15, 1222-1225.	2.4	0
18	Efficiency Re-Climbing in High-Current Droop Regime for Gallium-Nitride-based Light-Emitting Diodes. International Journal of High Speed Electronics and Systems, 2015, 24, 1520008.	0.7	0